Abstracts

A 0.2 µm GaAs MESFET Technology for 10 Gb/s Digital and Analog IC's

Y. Yamane, M. Ohhata, H. Kikuchi, K. Asai and Y. Imai. "A 0.2 µm GaAs MESFET Technology for 10 Gb/s Digital and Analog IC's." 1991 MTT-S International Microwave Symposium Digest 91.2 (1991 Vol. II [MWSYM]): 513-516.

A 0.2 µm gate length GaAs IC technology is reported. This technology enables the fabrication of both digital and analog K's using the same process. A 10 Gb/s decision circuit with a 130 mV sensitivity and 215 degree phase margin, and an amplifier with a 20 dB gain and 13 GHz bandwidth were successfully fabricated using this untied process technology.

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